

Silicon NPN Power Transistor

2N6834

DESCRIPTION

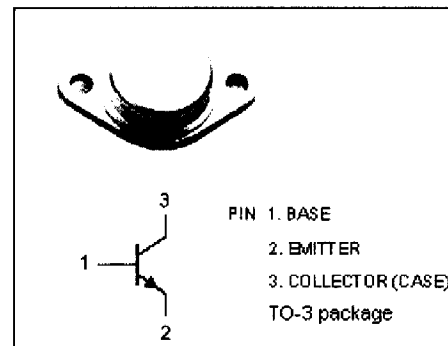
- Collector-Emitter Sustaining Voltage-
: $V_{CEO(SUS)} = 450V(\text{Min})$
- High Switching Speed

APPLICATIONS

- Designed for high-voltage ,high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switch-mode applications.

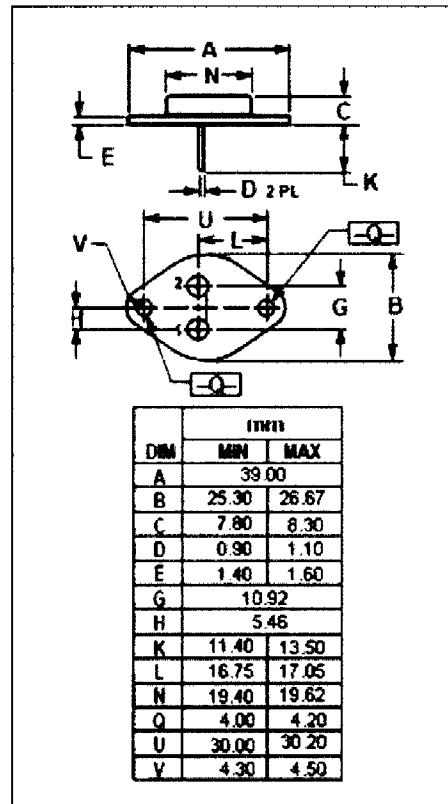
Typical applications:

- Switching regulators
- Inverters
- Solenoid and relay drivers
- Motor controls
- Deflection circuits



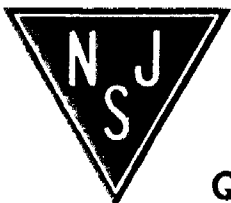
ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage	850	V
$V_{CEO(SUS)}$	Collector-Emitter Voltage	450	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	5	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	4	A
I_{BM}	Base Current-Peak	8	A
P_C	Collector Power Dissipation@ $T_C=25^\circ\text{C}$	125	W
T_J	Junction Temperature	200	$^\circ\text{C}$
T_{stg}	Storage Temperature	-65~200	$^\circ\text{C}$



THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-c}$	Thermal Resistance, Junction to Case	1.4	$^\circ\text{C/W}$



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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	$I_C=100\text{mA}; I_B=0$	450			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C=1.5\text{A}; I_B=0.15\text{A}$			1.0	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.4\text{A}$ $I_C=3\text{A}; I_B=0.4\text{A}, T_C=100^\circ\text{C}$			2.5 2.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C=3\text{A}; I_B=0.4\text{A}$ $I_C=3\text{A}; I_B=0.4\text{A}, T_C=100^\circ\text{C}$			1.5 1.5	V
I_{CEV}	Collector Cutoff Current	$V_{CEV}=850\text{V}; V_{BE(off)}=1.5\text{V}$ $V_{CEV}=850\text{V}; V_{BE(off)}=1.5\text{V}; T_C=100^\circ\text{C}$			0.25 1.5	mA
I_{CER}	Collector Cutoff Current	$V_{CE}=850\text{V}; R_{BE}=50\Omega, T_C=100^\circ\text{C}$			2.5	mA
I_{EBO}	Emitter Cutoff Current	$V_{EB}=6.0\text{V}; I_C=0$			1.0	mA
h_{FE-1}	DC Current Gain	$I_C=3\text{A}; V_{CE}=5\text{V}$	7.5		30	
h_{FE-2}	DC Current Gain	$I_C=5\text{A}; V_{CE}=5\text{V}$	5			
f_T	Current Gain-Bandwidth Product	$I_C=0.25\text{A}; V_{CE}=10\text{V}; f_{test}=10\text{MHz}$	15		75	MHz
C_{OB}	Output Capacitance	$I_E=0; V_{CB}=10\text{V}; f_{test}=1.0\text{kHz}$	20		200	pF

Switching times;Resistive Load

t_d	Delay Time	$I_C=3\text{A}, V_{CC}=250\text{V};$ $I_{B1}=0.4\text{A}; I_{B2}=-0.8\text{A};$ $P_W=30\mu\text{s}; R_{B2}=8\Omega$ Duty Cycle $\leq 2.0\%$		0.03	0.1	μs
t_r	Rise Time			0.1	0.3	μs
t_s	Storage Time			1.0	3.0	μs
t_f	Fall Time			0.06	0.3	μs